**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in an MLPAK33 (SOT8002) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- MLPAK33 package (3.3 x 3.3 mm footprint)

## 3. Applications

- · DC-to-DC converters
- Battery management
- · Low-side load-switch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	25	Α
Static chara	acteristics						·
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15.2 A; T <sub>j</sub> = 25 °C		-	3.9	4.7	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 13.5 A; T <sub>j</sub> = 25 °C		-	4.8	6	mΩ
Dynamic ch	naracteristics						<u>'</u>
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 15 V; $I_{D}$ = 13.5 A; $V_{GS}$ = 4.5 V; $T_{j}$ = 25 °C		-	14.7	22.1	nC

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	
2	S	source	ر ف ف ف	
3	S	source		D —
4	G	gate	]	
5	D	drain		G—UFIA)
6	D	drain	Laaad	mbb076 S
7	D	drain	8 7 6 5 MI DAK22 (SOT9002 4)	
8	D	drain	MLPAK33 (SOT8002-1)	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package						
	Name	Description	Version				
PXN4R7-30QL		plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-1				

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PXN4R7-30QL	8AN

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## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	25	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	15	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	9.6	Α
		V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	74	Α
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	125	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	4.8	W
		T <sub>amb</sub> = 25 °C	[1]	-	1.8	W
		T <sub>sp</sub> = 25 °C		-	42	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	n diode		'	1		
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.8	Α

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

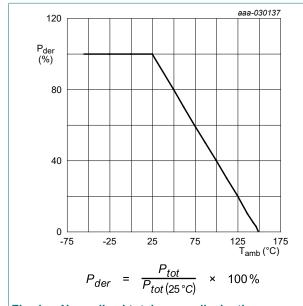


Fig. 1. Normalized total power dissipation as a function of ambient temperature

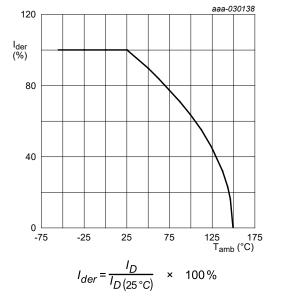


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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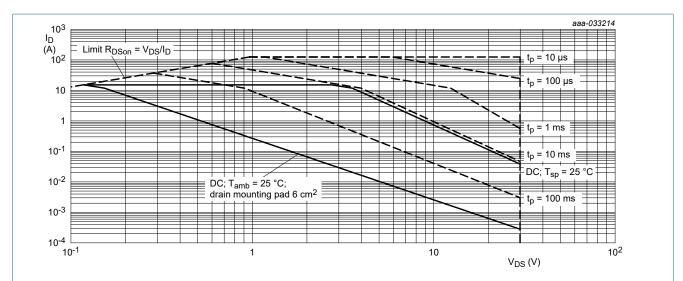


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

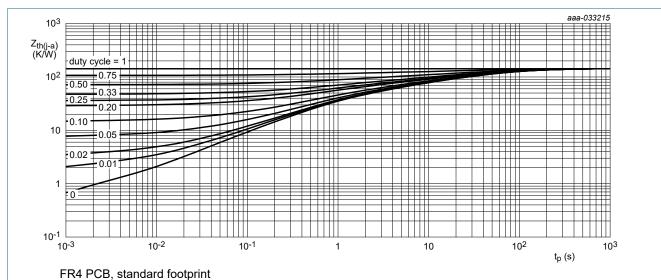
30 V, N-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	145	185	K/W
	junction to ambient		[2]	-	55	70	K/W
		in free air; t ≤ 5 s	[2]	-	21	26	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	2.3	3	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



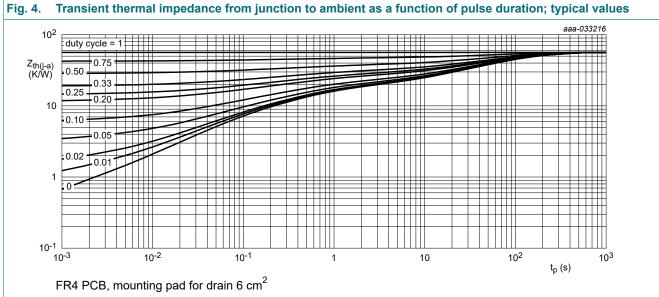


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

#### **Table 7. Characteristics**

Parameter	Conditions	Min	Тур	Max	Unit
cteristics					
drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.6	2.5	V
drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15.2 A; T <sub>j</sub> = 25 °C	-	3.9	4.7	mΩ
resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15.2 A; T <sub>j</sub> = 150 °C	-	6.4	7.7	mΩ
	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 13.5 A; T <sub>j</sub> = 25 °C	-	4.8	6	mΩ
forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 15.2 \text{ A}; T_j = 25 \text{ °C}$	-	42	-	S
gate resistance	f = 1 MHz	-	0.7	-	Ω
aracteristics		'			
total gate charge	$V_{DS}$ = 15 V; $I_{D}$ = 15.2 A; $V_{GS}$ = 10 V; $T_{j}$ = 25 °C	-	30.8	46.2	nC
	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 13.5 A; V <sub>GS</sub> = 4.5 V;	-	14.7	22.1	nC
gate-source charge	T <sub>j</sub> = 25 °C	-	5	-	nC
pre-threshold gate- source charge		-	3	-	nC
post-threshold gate- source charge		-	2	-	nC
gate-drain charge	1	-	4.1	-	nC
gate-source plateau voltage	$V_{DS} = 15 \text{ V}; I_D = 13.5 \text{ A}; T_j = 25 \text{ °C}$	-	2.6	-	V
input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	2100	-	pF
output capacitance	T <sub>j</sub> = 25 °C	-	350	-	pF
reverse transfer capacitance		-	122	-	pF
turn-on delay time	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 13.5 A; V <sub>GS</sub> = 4.5 V;	-	11	-	ns
rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	15	-	ns
turn-off delay time	]	-	13	-	ns
fall time	1	-	6	-	ns
n diode		'			
source-drain voltage	I <sub>S</sub> = 1.8 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.7	1.2	V
reverse recovery time	I <sub>S</sub> = 1.8 A; dI <sub>S</sub> /dt = -100 A/μs;	-	21	-	ns
recovered charge	$V_{GS} = 4.5 \text{ V}; V_{DS} = 15 \text{ V}; T_j = 25 \text{ °C}$	-	13	-	nC
reverse recovery rise time		-	14	-	ns
	-		7		_
	drain-source breakdown voltage  gate-source threshold voltage  drain leakage current  gate leakage current  drain-source on-state resistance  forward transconductance gate resistance  aracteristics  total gate charge  pre-threshold gate- source charge post-threshold gate- source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time fall time  n diode  source-drain voltage reverse recovery time recovered charge reverse recovery rise	cteristics         drain-source breakdown voltage $I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$ gate-source threshold voltage $I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}$ drain leakage current $V_{DS} = 30 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$ gate leakage current $V_{GS} = 20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$ drain-source on-state resistance $V_{GS} = 10 \ V; \ I_D = 15.2 \ A; \ T_j = 25 \ ^{\circ}\text{C}$ $V_{GS} = 10 \ V; \ I_D = 15.2 \ A; \ T_j = 150 \ ^{\circ}\text{C}$ $V_{GS} = 10 \ V; \ I_D = 15.2 \ A; \ T_j = 25 \ ^{\circ}\text{C}$ $V_{GS} = 10 \ V; \ I_D = 15.2 \ A; \ T_j = 25 \ ^{\circ}\text{C}$ $V_{DS} = 10 \ V; \ I_D = 15.2 \ A; \ T_j = 25 \ ^{\circ}\text{C}$ $V_{DS} = 15 \ V; \ I_D = 15.2 \ A; \ V_{GS} = 10 \ V; \ T_j = 25 \ ^{\circ}\text{C}$ $V_{DS} = 15 \ V; \ I_D = 13.5 \ A; \ V_{GS} = 4.5 \ V; \ T_j = 25 \ ^{\circ}\text{C}$ $V_{DS} = 15 \ V; \ I_D = 13.5 \ A; \ V_{GS} = 4.5 \ V; \ T_j = 25 \ ^{\circ}\text{C}$ $V_{DS} = 15 \ V; \ I_D = 13.5 \ A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$ $V_{DS} = 15 \ V; \ I_D = 13.5 \ A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$ $V_{DS} = 15 \ V; \ I_D = 13.5 \ A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$ $V_{DS} = 15 \ V; \ I_D = 13.5 \ A; \ V_{GS} = 4.5 \ V; \ V_{GS} = 4.5$		cteristics           drain-source breakdown voltage gate-source threshold voltage gate-source threshold voltage $I_D = 250  \mu A;  V_{DS} = V_{GS};  T_j = 25  ^{\circ}C$ 1         1.6           drain leakage current voltage $V_{DS} = 30  V;  V_{DS} = 0  V;  T_j = 25  ^{\circ}C$ -         -           gate leakage current voltage $V_{GS} = 20  V;  V_{DS} = 0  V;  T_j = 25  ^{\circ}C$ -         -           drain-source on-state resistance $V_{GS} = 10  V;  I_D = 15.2  A;  T_j = 125  ^{\circ}C$ -         -           drain-source on-state resistance $V_{GS} = 10  V;  I_D = 15.2  A;  T_j = 150  ^{\circ}C$ -         -         -           drain-source on-state resistance $V_{GS} = 10  V;  I_D = 15.2  A;  T_j = 150  ^{\circ}C$ -         -         6.4 $V_{GS} = 10  V;  I_D = 15.2  A;  V_{GS} = 10  V;  V_{DS} = 15  V;  I_D = 15.2  A;  V_{GS} = 10  V;  V_{DS} = 15  V;  V_{DS} = 15  V;  V_{DS} = 10  V;  V_{DS} $	Content   Con

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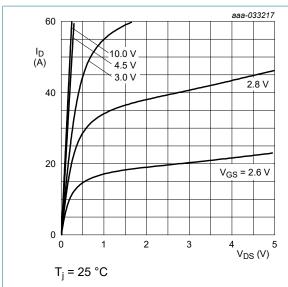


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

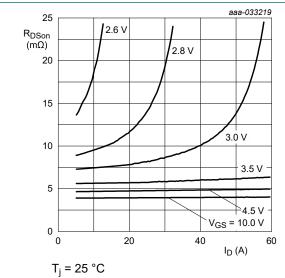


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

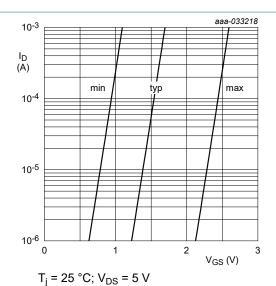


Fig. 7. Subthreshold drain current as a function of gate-source voltage

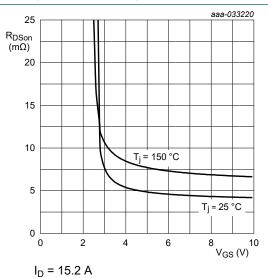


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 30 V, N-channel Trench MOSFET

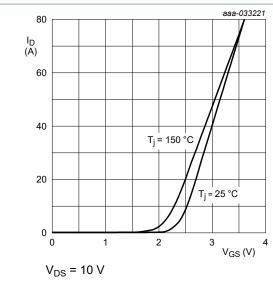


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

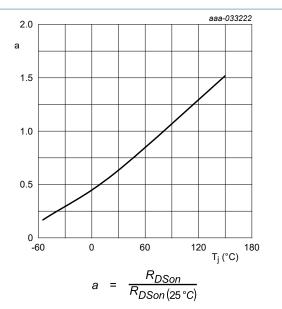


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

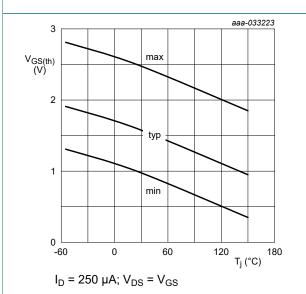


Fig. 12. Gate-source threshold voltage as a function of junction temperature

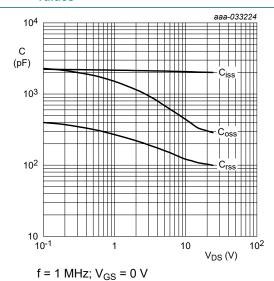


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### 30 V, N-channel Trench MOSFET

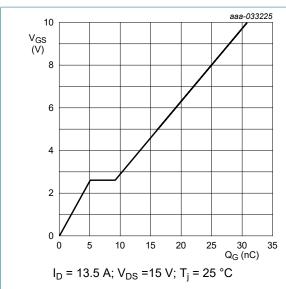


Fig. 14. Gate-source voltage as a function of gate charge; typical values

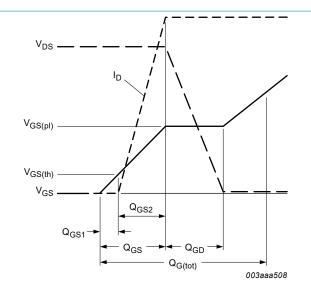


Fig. 15. Gate charge waveform definitions

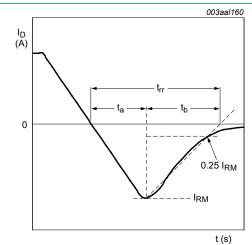


Fig. 16. Reverse recovery timing definition

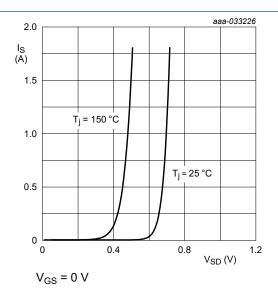
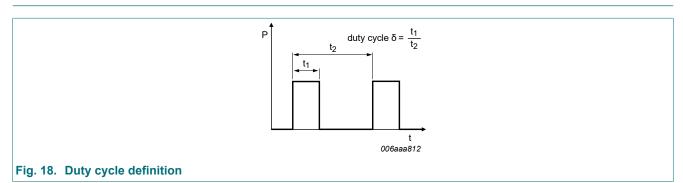


Fig. 17. Source current as a function of source-drain voltage; typical values

### 11. Test information



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# 12. Package outline

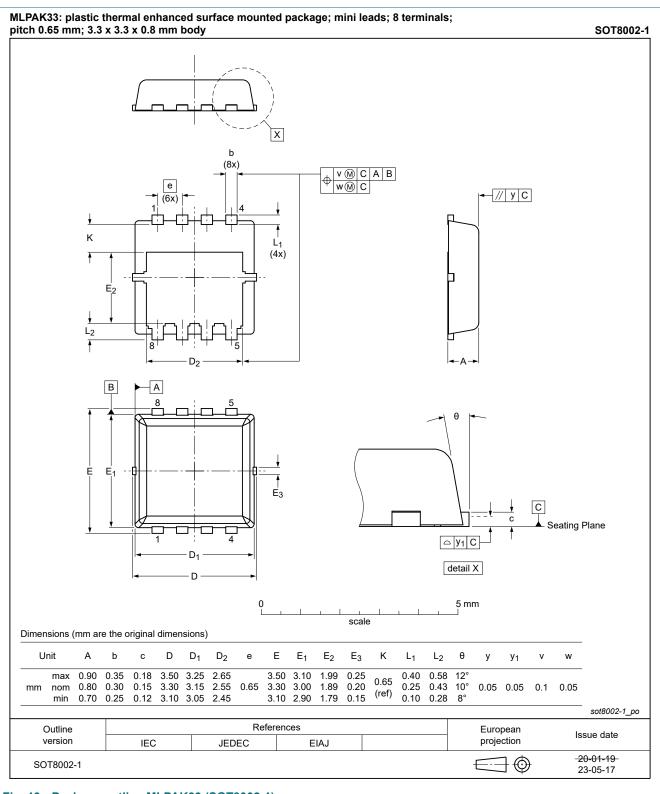
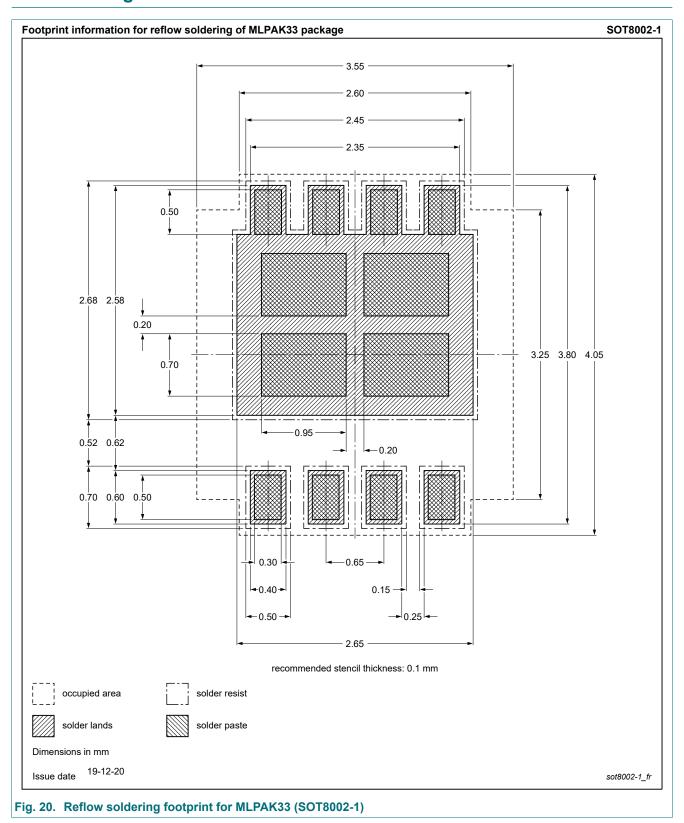


Fig. 19. Package outline MLPAK33 (SOT8002-1)

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# 13. Soldering



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# 14. Revision history

#### **Table 8. Revision history**

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Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PXN4R7-30QL v.2	20230731	Product data sheet	-	PXN4R7-30QL v.1			
Modifications:	Chapter "Package o	Chapter "Package outline": drawing update					
PXN4R7-30QL v.1	20210415	Product data sheet	-	-			

#### 30 V, N-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### 30 V, N-channel Trench MOSFET

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